Table of Contents

To Use this Index: Scroll down or use the bookmarks in the left-hand frame to move to a new location in this index. Click on a **blue paper title** to view that paper. To return to this index after viewing a paper, click the PREVIOUS MENU bookmark in the left frame.

SESSION 1: PROCESS CHARACTERIZATION

Co-Chairs: Christopher Hess, PDF Solutions and Kelvin Yih-Yuh Doong, Taiwan Semiconductor Manufacturing Co.

1.1 **Ring-gate MOSFET Test Structures for Measuring Surface-Charge-Layer Sheet Resistance on High-Resistivity-Silicon Substrates,** S.B. Evseev, L.K. Nanver and S. Milosavljevic, *DIMES, Delft University of Technology, Delft, The Netherlands* **3**

1.2 **−1/+0.8°C Error, Accurate Temperature Sensor using 90nm 1V CMOS for On-line Thermal Monitoring of VLSI Circuits,** M. Sasaki, M. Ikeda and K. Asada, *The University of Tokyo, Tokyo, Japan* **9**

1.3 **Specific Contact Resistance Measurements of Metal-Semiconductor Junctions,** N. Stavitski, M.J.H. van Dal* R.A.M. Wolters, A.Y. Kovalgin, J. Schmitz, *University of Twente, Enschede, The Netherlands and * Philips Research, Leuven, Belgium* **13**

1.4 **Test Structures for Study of Electron Transport in 40 - 100-nm Nickel Silicide Features,** B. Li, L. Shi, JP. Zhou, P.S. Ho, R.A. Allen*, and M.W. Cresswell*, *The University of Texas at Austin, Austin, TX and *National Instutite of Standards and Technology, Gaithersburg, MD* **18**

SESSION 2: PARAMETER EXTRACTION

Co-Chairs: Kevin McCarthy, University College Cork and Kjell Jeppson, Chalmers University of Technology

2.1 **A New Polysilicon Resistor Model considering Geometry Dependent Voltage Characteristics for the Deep Sub-Micron CMOS Process,** S.Y. Ko, J.S. Kim, G.H. Lim, S.K Kim, *DongbuAnam Semiconductor, Gyeonggi-Do, South Korea* **27**

2.2 **Test Structures and Measurement of Gate Sidewall Junction Capacitance in MOSFETs,** N. Hasegawa, S. Yamaura, T. Mori, and S. Yamaguchi*, *Fujitsu Laboratories, Ltd., Kawasaki, Japan and *Fujitsu ltd., Tokyo, Japan* **31**

2.3 **New Test Structures for Extraction of Base Sheet Resistance in BiCMOS Technology,** C. Raya, F. Pourchon, D. Celi, M. Laurens, T. Zimmer*, *ST Microelectronics, Crolles, France and *Université Bordeaux, Talence, France* **35**

SESSION 3: MEMORY

Co-Chairs: Yoichi Tamaki, Hitachi Ltd. and Larg Weiland, PDF Solutions, Inc.

3.1 **Measurement Method for Transient Programming Current of 1T1R Phase-change Memory,** K. Kurotsuchi, N. Takaura, N. Matsuzaki, Y. Matusi, O. Tonomura, Y. Fujisaki, N. Kitai*, R. Takemura, K. Osada, S. Hanzawa, H. Moriya, T. Iwasaki, T. Kawahara, M. Terao, M. Matsuoka**, and M. Moniwa**, *Hitachi, Ltd., Tokyo, Japan, *Hitachi ULSI Systems, Tokyo, Japan, and ** Renesas Technology Corp., Hyogo, Japan* — 43

3.2 **Investigation of Lateral Charge Distribution of 2-bit SONOS Memory Devices Using Physically Separated Twin SONOS Structure,** B.Y. Choi, C.-H. Lee*, Y.K. Lee**, H. Shin, J.D. Lee, B.-G. Park, D.-W. Kim*, S.-K. Sung*, S.-H. Lee*, B.-K. Cho*, T.-Y. Kim*, E.S. Cho*, J.J. Lee*, and D. Park*, *Seoul National University, Seoul, Korea, *Samsung Electronics Co., Ltd., Gyeonggi-do, Korea, and **Stanford University, Stanford, CA* — 47

3.3 **On the Passivation of Interface States in SONOS Test Structures: Impact of Device Layout and Annealing Process,** F. Driussi, L. Selmi, N. Akil*, M.J. Van Duuren*, and R. Van Schaijk* *DIEGM, University of Udine, Udine, Italy and * Philips Research, Leuven, Belgium* — 51

SESSION 4– RF

Co-Chairs: Franz Sischka, Agilent Home Office and H-D. Lee, Chungnam National University

4.1 **Characterisation of Advanced Multilayer De-embedding Structures up to 50 GHz Incorporating a Novel Validation Standard,** J.A. O'Sullivan, K.G. McCarthy and P.J. Murphy, *University College Cork, Cork, Ireland* — 59

4.2 **Analysis and Modeling of Substrate Impedance Network in RF CMOS,** E. Bouhana, P. Scheer, S. Boret, D. Gloria, G. Dambrine*, M. Minondo and H. Jaouen, *STMicroelectronics, Crolles, France and *IEMN, Villeneuve d'Ascq, France* — 65

4.3 **Impact of GHz Disturbances on DC Parametric Measurements,** H.P. Tuinhout and P.G.M. Baltus*, *Philips Research, Eindhoven, The Netherlands and *Philips Semiconductors, Eindhoven, The Netherlands* — 71

4.4 **Impact of Pad De-embedding on the Extraction of Interconnects Parameters,** S. Han, J. Kim and D.P. Neikirk, *The University of Texas at Austin, Austin, TX* — 76

SESSION 5: RF NOISE PANEL

Chair: Colin McAndrew, Motorola

SESSION 6: YIELD

Co-Chairs: Ulrich Shaper, Infineon Technologies AG and Satoshi Habu, Agilent Technolgies Japan, Ltd.

6.1 **Ring Oscillator Based Technique for Measuring Variability Statistics**, M. Bhushan, M.B. Ketchen*, S. Polonsky* and A. Gattiker**, *IBM Sytems and Technology Group, Poughkeepsie, NY, *IBM T.J. Watson Research Center, Yorktown Heights, NY and **IBM Austin Research Lab., Austin, TX* **87**

6.2 **Methodology for Characterizing the Impact of Circuit Layout, Technology Options, Device Engineering and Temperature on the Circuit Power-Delay Characteristics**, T. Chiarella, J. Ramos, A. Nackaerts, S. Demuynck, S. Verhaegen, R. Verbeeck, M. de Potter de ten Broeck, C. Kerner, T. Hoffmann, M. Van Hove, I. Debusschere, and S. Biesemans, *IMEC, Leuven, Belgium* **93**

6.3 **Field-Configurable Test Structure Array (FC-TSA): Enabling Design for Monitor, Model and Manufacturability**, K.Y.Y. Doong, J. Bordelon*, K-J. Chang**, L.J. Hung, C.C. Liao, S.C. Lin, P.S. Ho, S. Hsieh, and K.L. Young, *Taiwan Semiconductor Manufacturing Corporation, Shinchu, Taiwan, *Stratosphere Solutions, Inc., Sunnyvale, CA and **National Tsing Hua University, Shin-chu, Taiwan* **98**

6.4 **A 65nm Random and Systematic Yield Ramp Infrastructure Utilizing a Specialized Addressable Array with Integrated Analysis Software**, M. Karthikeyan, S. Fox, W. Cote, G. Yeric*, M. Hall*, J. Garcia**, B. Mitchell**, E. Wolf***, and S. Agarwal#, *IBM Systems and Technology Group, Hopewell Junction, NY, *Synopsys, Austin, TX,**Synopsys, Dallas, TX, ***Synopsys, Marlboro, MA, and #now with Pyxys, Austin, TX* **104**

6.5 **Scribe Characterization Vehicle Test Chip for Ultra Fast Product Wafer Yield Monitoring**, C. Hess, A. Inani, Y. Lin, M. Squicciarini*, R. Lindley**, N. Akiya***, *PDF Solutions, Inc. San Jose, CA, *PDF Solutions, Desenzano, Italy, ** PDF Solutions, San Diego, CA, and *** PDF Solutions, Kanagawa, Japan* **110**

SESSION 7: CD METROLOGY

Co-Chairs: Loren Linholm and A.J. Walton, University of Edinburgh

7.2 **Comparison of Optical and Electrical Measurement Techniques for CD Metrology on Alternating Aperture Phase-Shifting Masks**, S. Smith, A. Tsiamis, M. McCallum*, A.C. Hourd**, J.T.M. Stevenson, and A.J. Walton, The *University of Edinburgh, Edinburgh, United Kingdom, *Nikon Precision Europe, Livingston, United Kingdom and **Compugraphics International Ltd., Fife, United Kingdom* **117**

7.3 **Design and Fabrication of a Copper Test Structure for Use as an Electrical Critical Dimension Reference**, B.J.R. Shulver, A.S. Bunting, A.M. Gundlach, L.I. Haworth, A.W.S. Ross, A.J. Snell, J.T.M. Stevenson, A.J. Walton, R.A. Allen*, and M.W. Cresswell*, *University of Edinburgh, Edinburgh, United Kingdom and *NIST, Gaithersburg, MD* **124**

SESSION 8 – MEMS

Co-Chairs: Yoshio Mita, University of Tokyo and Robert Ashton, White Mountain Labs

8.1 **Characterization of Dielectric Charging in RF MEMS Capacitive Switches,** R.W. Herfst, H.G.A. Huizing, P.G. Steeneken, and J. Schmitz*, *Philips Research Laboratories, Eindhoven, The Netherlands and *University of Twente, Enschede, The Netherlands* **133**

8.2 **MEMS Test Structure for Measuring Thermal Conductivity of Thin Films,** L. La Spina, N. Nenadovic, A. W. van Herwaarden*, H. Schellevis, W. H. A. Wien, and L. K. Nanver, *DIMES - Delft University of Technology, Delft, The Netherlands and *Xensor Integration, Delft, The Netherlands* **137**

8.3 **Test Structures for the Characterisation of MEMS and CMOS Integration Technology,** H. Lin, A.J. Walton, C.C. Dunare, J.T.M. Stevenson, A.M. Gundlach, S. Smith, and A.S. Bunting, *University of Edinburgh, Edinburgh, United Kingdom* **143**

8.4 **A Bulk Knife-Edged As-Deposition Self-Patterning Structure for Greek-Cross and Organic Thin Film Transistors,** T. Harada, K. Ito, T. Shibata and Y. Mita, *University of Tokyo, Tokyo Japan* **149**

SESSION 9 – MATCHING

Co-Chairs: Hans P. Tuinhout, Philips Research and Mark Poulter, National Semiconductor Corp.

9.1 **Impact of Emitter Resistance Mismatch on Base and Collector Current Matching in Bipolar Transistors,** S. Danaie, A. Perrotin, G. Ghibaudo*, J-C. Vildeuil, G. Morin, and M. Laurens, *STMicroelectronics, Crolles, France and *IMEP/CNRS, Grenoble, France* **157**

9.2 **High-Frequency Measurements of the Mismatch on the Y-parameters of High-Speed SiGe:C HBTs,** L.J. Choi, R. Venegas and S. Decoutere, *IMEC, Leuven, Belgium* **163**

9.3 **High Frequency Mismatch Characterization on 170 GHz HBT NPN Bipolar Device,** A. Perrotin, D. Gloria, S. Danaie, F. Pourchon, and M. Laurens, *STMicroelectronics, Crolles, France* **169**

9.4 **Improved Methodology for Better Accuracy on Transistors Matching Characterization,** A. Cathignol, K. Rochereau**, S. Bordez, and G. Ghibaudo*, *STMicroelectronics, Crolles, France, *IMEP, Grenoble, France, and **Philips Semicondctors, Crolles, France* **173**

SESSION 10– DEVICE CHARACTERIZATION

Co-Chairs: Yoshiaki Hagiwara, Sony Corp. and Charles N. Alcorn, BAE Systems

10.1 **Test Structure Design for Measuring Electron and Hole Mobilities at Very High Injection Levels,** G.D. Licciardo, *University of Salerno, Salerno, Italy* **181**

10.2 **A Test Structure to Separately Analyze CMOSFET Reliabilities Around Center and Edge Along the Channel Width,** T. Ohzone, E. Ishii, T. Morishita, K. Komoku, T. Matsuda* and H. Iwata*, *Okayama Prefectural University, Okayama, Japan and *Toyama Prefectural University, Toyama, Japan* **187**

10.3 **1/F Gate Tunneling Current Noise Model of Ultrathin Oxide MOSFETs,** F. Martinez, S. Soliveres, C. Leyris, M. Valenza, *CEM2 – Universite Montpellier II, Montpellier, France* **193**

10.4 **Dielectric Relaxation Characterization and Modeling in Large Frequency and Temperature Domain: Application to 5 fF/µm² Ta_2O_5 MIM Capacitor,** J-P. Manceau, S. Bruyère, E. Picollet, M. Minondo, C. Grundrich, D. Cottin, M. Bely, *STMicroelectronics, Crolles, France* **199**

10.5 **Impact of Neighbor Components Heating on Power Transistor Electrical Behavior,** H. Beckrich, S. Ortolland, D. Pache, D. Céli, D. Gloria, T. Zimmer*, *STMicroelectronics, Crolles, France and *Université Bordeaux, Talence, France* **205**

SESSION 11 – CAPACITANCE

Co-Chairs: Jurrian Schmitz, University of Twente and Yoshiaki Hagiwara, Sony Corporation

11.1 **Analogue Characterization of Horizontal Bars Capacitors for Smart Power Applications,** Z. Ning, H.-X. Delecourt, L. De Schepper, D. Tack, B. Desoete, and R. Gillon, *AMI Semiconductor, Oudenaarde, Belgium* **213**

11.2 **Novel Test Structures for On-Chip Characterization of Coupling Capacitance Variation by In-and Anti-Phase Crosstalk in Multi-Level Metallization,** H-D. Lee, I-S. Han, T-G. Goo, H-H. Ji, I-S. Han, H-S. Joo, D-M. Kim*, S-H. Park**, H-S. Lee**, W-J. Ho**, D-B. Kim**, I-H. Cho**, S-Y. Kim**, S-B. Hwang**, J-G. Lee**, and J-W. Park**, *Chungnam National University, Daejeon, Korea, *Korea Institute for Advanced Study, Seoul, Korea and **MagnaChip Semiconductor Inc., Choongbuk, Korea* **218**

11.3 **A Comprehensive Model to Accurately Calculate the Gate Capacitance and The Leakage from DC to 100 MHz for Ultra Thin Dielectrics,** L. Pantisano, J. Ramos, W. San Andres Serrano, Ph.J. Roussel, W. Sansen*and G. Groeseneken, *IMEC, Leuven, Belgium and *University of Leuven, Leuven Belgium* **222**

11.4 **C-V Test Structures for Metal Gate CMOS,** R. Bankras, M. Tiggelman, M.A. Negara*, G.T. Sasse, and J. Schmitz, *University of Twente, Enschede, The Netherlands* **226**

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